LAPT 2SC2922

Silicon NPN Epitaxial Planar Transistor (Complement to type 2SA1216)

Application : Audio and General Purpose

■ **Absolute maximum ratings** (Ta=25°C)

Symbol	Ratings	Unit
V_{CBO}	180	V
V_{CEO}	180	V
V_{EBO}	5	V
I_C	17	A
I_B	5	A
P_C	200(Tc=25°C)	W
Tj	150	°C
Tstg	−55 to +150	°C

■ **Electrical Characteristics** (Ta=25°C)

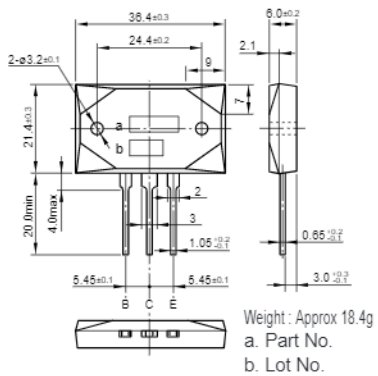
Symbol	Conditions	Ratings	Unit
I_{CBO}	V_{CB}=180V	100max	∝A
I_{EBO}	V_{EB}=5V	100max	∝A
$V_{(BR)CEO}$	I_C=25mA	180min	V
h_{FE}	V_{CE}=4V, I_C=8V	30min*	
$V_{CE(sat)}$	I_C=8A, I_B=0.8A	2.0max	V
f_T	V_{CE}=12V, I_E=−2A	50typ	MHz
C_{OB}	V_{CB}=10V, f=1MHz	250typ	pF

*h_{FE} Rank O(30 to 60), Y(50 to 100), P(70 to 140), G(90 to 180)

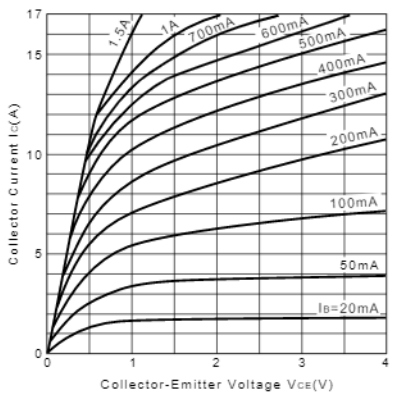
■ **Typical Switching Characteristics (Common Emitter)**

V_{CC} (V)	R_L (Ω)	I_C (A)	V_{B2} (V)	I_{B1} (A)	I_{B2} (A)	ton (∝s)	tstg (∝s)	tf (∝s)
40	4	10	−5	1	−1	0.2typ	1.3typ	0.45typ

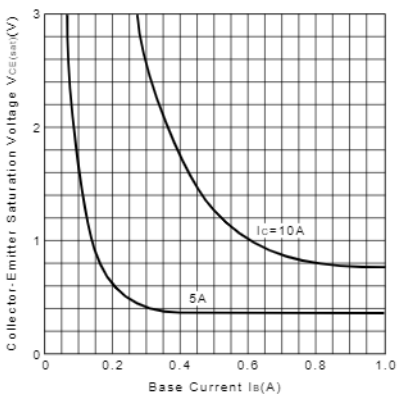
External Dimensions MT-200



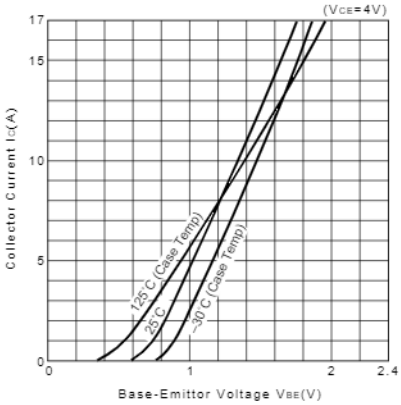
I_C−V_{CE} Characteristics (Typical)



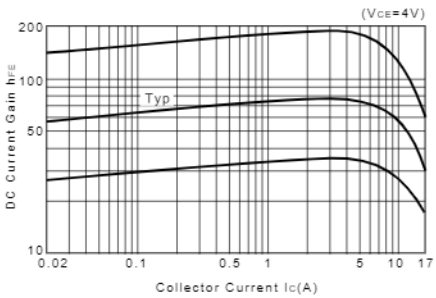
$V_{CE(sat)}$−I_B Characteristics (Typical)



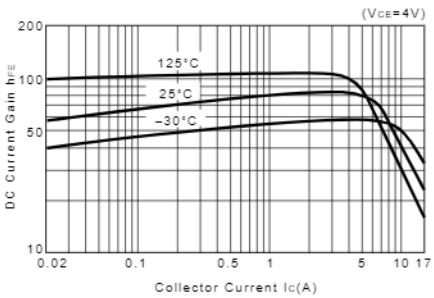
I_C−V_{BE} Temperature Characteristics (Typical)



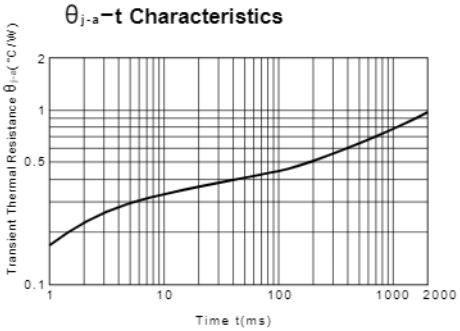
h_{FE}−I_C Characteristics (Typical)



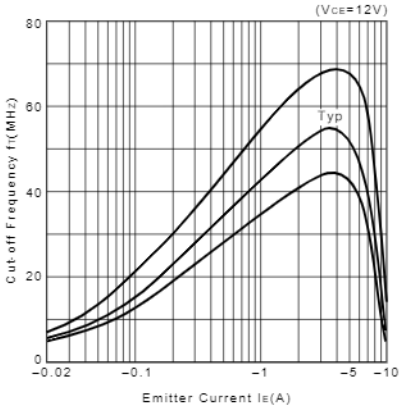
h_{FE}−I_C Temperature Characteristics (Typical)



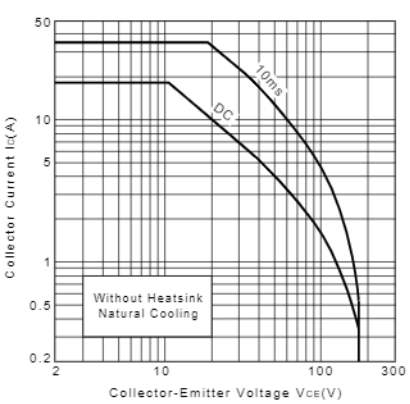
$\theta_{j\text{-}a}$−t Characteristics



f_T−I_E Characteristics (Typical)



Safe Operating Area (Single Pulse)



Pc−Ta Derating

